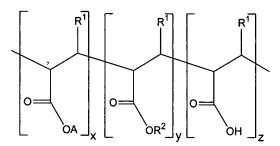
What is claimed is:

- 1. A ferroelectric film precursor composition, comprising
 - a ferroelectric polymer or prepolymer,
 - a casting solvent, and
 - a leveling agent comprising a (meth)acrylic copolymer represented by formula (I):



wherein

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each R1 is independently a hydrogen or methyl group,

A is
$$-CR^3R^4R^5$$
,

10 wherein

each R^3 is independently a hydrogen, substituted or unsubstituted C_1 - C_{20} linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, and

each R^4 and R^5 is independently a hydrogen, substituted or unsubstituted C_1 - C_{20} linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety or R^4 and R^5 together form a C_3 - C_8 cycloalkyl group, with the proviso that when R^4 and R^5 are each hydrogen, R^3 is not a linear alkyl group;

 R^2 comprises a substituted or unsubstituted C_1 - C_{20} linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, wherein the substituents on R^2 , R^3 , R^4 , and R^5 may be halogen, hydroxyl, cyano, nitro, C_1 - C_{12} alkyl carboxy ester, acyl, C_1 - C_{12} alkoxy, carboxylate, or a mixture comprising one or more of the foregoing groups;

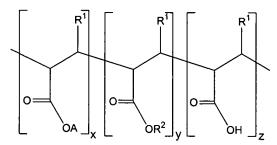
x+y+z = 100 mol%;

x and y are each independently 10 to 70 mol%; and z is less than or equal to 40 mol%.

- 2. The composition of claim 1, wherein A has the formula $-CH_2CR^4R^5$, R^4 and R^5 are each independently a C_1-C_{10} linear or branched alkyl, alkenyl, or alkaryl group, or a C_3-C_{10} cycloalkyl or cycloalkenyl group.
- 3. The composition of Claim 1, wherein R^4 or R^5 or both comprises a site of unsaturation.
- 5 4. The composition of claim 1, wherein the ferroelectric polymer comprises a vinylidene fluoride-containing polymer.
 - 5. A process for forming a ferroelectric polymer film, the process comprising: disposing a casting composition comprising a ferroelectric polymer, a casting solvent, and the leveling agent of claim 1 onto a substrate, and

removing at least a portion of the casting solvent composition to produce the ferroelectric polymer film.

- 6. The process of claim 5, wherein the ferroelectric polymer film has an atomic force microscopy roughness of less than 300 Angstroms, a polydispersity of less than 3, and a Curie transition temperature of greater than 90 degrees Celsius.
- 15 7. A ferroelectric polymer film, comprising:
 - a ferroelectric polymer; and
 - a leveling agent comprising a (meth)acrylic copolymer represented by formula (I):



wherein

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20 each R¹ is independently a hydrogen or methyl group,

A is $-CR^3R^4R^5$,

wherein

each R³ is independently a hydrogen, substituted or unsubstituted C₁-C₂₀ linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, and each R⁴ and R⁵ is independently a hydrogen, substituted or unsubstituted C₁-C₂₀ linear or branched chain linear or branched chain

alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety or R⁴ and R⁵ together form a C₃-C₈ cycloalkyl group, with the proviso that when R⁴ and R⁵ are each hydrogen, R³ is not a linear alkyl group;

- R² comprises a substituted or unsubstituted C₁-C₂₀ linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, wherein the substituents on R², R³, R⁴, and R⁵ may be halogen, hydroxyl, cyano, nitro, C₁-C₁₂ alkyl carboxy ester, acyl, C₁-C₁₂ alkoxy, carboxylate, or a mixture comprising one or more of the foregoing groups;
- 10 x+y+z = 100 mol%;x and y are each independently 10 to 70 mol%; and z is less than or equal to 40 mol%.

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- 8. A data processing device comprising the film of claim 7.
- 9. The data processing device of claim 8 wherein the film is disposed between a plurality of electrodes.
 - 10. A film stack comprising the ferroelectric polymer film of claim 7 disposed on a substrate.
 - 11. A data processing device comprising the film stack of claim 10.